1.0 General Description

The new AMIS-4168x is an interface between the protocol controller and the physical wires of the bus lines in a control area network (CAN).

The new AMIS-41683 is identical to the AMIS-41682 but has a true 3.3V digital interface to the CAN controller.

The device provides differential transmit capability but will switch in error conditions to single-wire transmitter and/or receiver. Initially it will be used for low speed applications, up to 125kBaud, in passenger cars.

The AMIS-41682 is implemented in I2T100 technology enabling both high-voltage analog circuitry and digital functionality to co-exist on the same chip.

This product consolidates the expertise of AMIS for in car multiplex transceivers and supports together with AMIS-30522 (VAN), AMIS-30660 and AMIS-30663 (CAN High Speed), and AMIS-30600 (LIN) another widely used physical layer.

2.0 Key Features

- Optimized for in-car low-speed communication
 - Baud rate up to 125kBaud
 - Up to 32 nodes can be connected
 - Due to built-in slope control function and a very good matching of the CANL and CANH bus outputs this device realizes a very low electro magnetic emission (EME)
 - Fully integrated receiver filters
 - Permanent dominant monitoring of transmit data input
 - Differential receiver with wide common-mode range for high electro magnetic susceptibility (EMS) in normal- and low-powermodes
 - True 3.3V digital I/O interface to CAN controller for AMIS-41683 only
- · Management in case of bus failure
 - \circ In the event of bus failures, automatic switching to single-wire

- mode, even when the CANH bus wire is short circuited to Vcc
- The device will automatically reset to differential mode if the bus failure is removed
- During failure modes there is full wake-up capability
- Un-powered nodes do not disturb bus lines
- · Protection issues
 - Short circuit proof to battery and ground
 - Thermal protection
 - The bus lines are protected against transients in an automotive environment
- An un-powered node does not disturb the bus lines
- Support for low power modes
 - Low current sleep and standby mode with wake-up via the bus lines
 - Power-on-reset flag on the output
 - o Two-edge sensitive wake-up input signal via pin SLEEP

3.0 Technical Characteristics

Table 1: Technical Characteristics

Symbol	Parameter	Conditions	Min.	Max.	Unit
Vcanh	DC voltage at pin CANH, CANL	0 < VCC < 5.25V; no time limit	-40	+40	V
Vbat	Voltage at pin Vbat	Load dump		+40	V

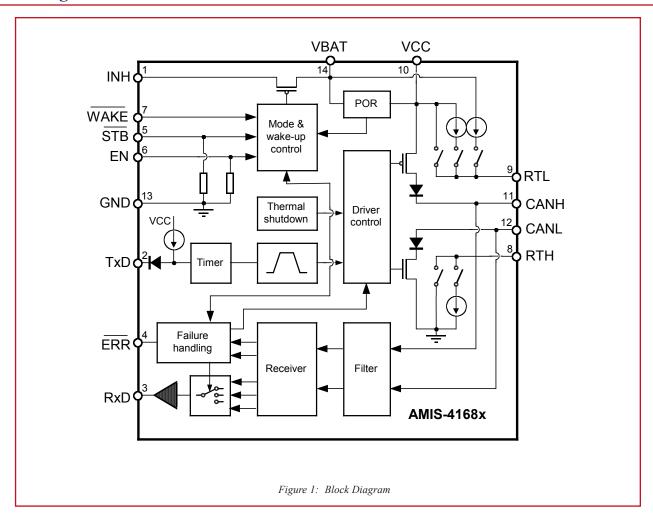
4.0 Ordering Information

Table 2: Ordering Information

Ordering Code	Marketing Name	Package	Temp Range
D2CANM	AMIS41682AGA	SOIC-14 GREEN	-40°C125°C
C2CANN	AMIS41683AGA	SOIC-14 GREEN	-40°C125°C

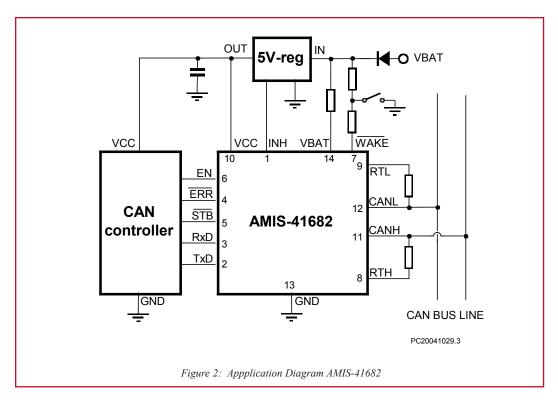


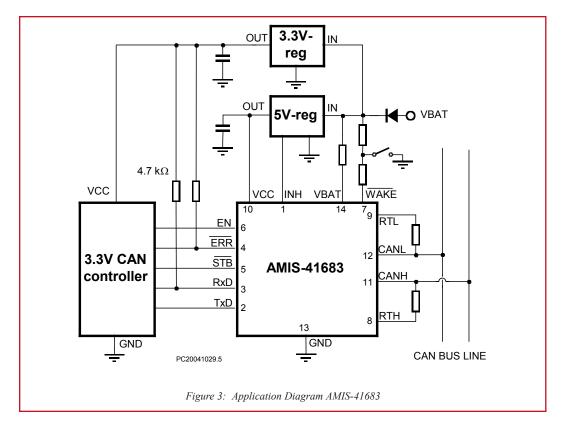
5.0 Block Diagram



6.0 Typical Application Schematic

6.1 Application Schematic





6.2 Pin Description

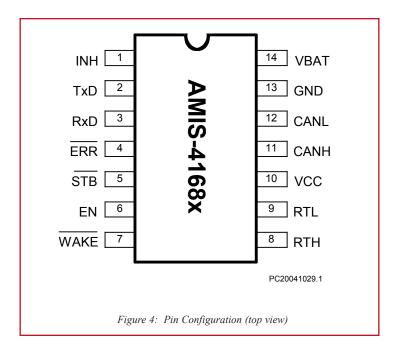


Table 3: Pin Description

Pin	Name	Description
1	INH	Inhibit output for external voltage regulator
2	TxD	Transmit data input; internal pull-up current
3	RxD	Receive data output
4	ERR-B	Error; wake-up and power-on flag; active low
5	STB-B	Standby digital control input; active low; pull-down resistor
6	EN	Standby digital control input; active high; pull-down resistor
7	WAKE-B	Enable digital control input; falling and rising edges are both detected
8	RTH	Pin for external termination resistor at CANH
9	RTL	Pin for external termination resistor at CANL
10	Vcc	5V supply input
11	CANH	Bus line; high in dominant state
12	CANL	Bus line; low in dominant state
13	GND	Ground
14	BAT	Battery supply

Note: Functional description and characteristics are made for the AMIS-41682 but are also valid for the AMIS-41683. The difference between the two devices is explicitly mentioned in text.

7.0 Functional Description

7.1 Description

AMIS-41682 is a fault tolerant CAN transceiver which works as an interface between the CAN protocol controller and the physical wires of the CAN bus (see Figure 2). It is primarily intended for low speed applications, up to 125kBaud, in passenger cars. The device provides differential transmit capability to the CAN bus and differential receive capability to the CAN controller.

The AMIS-41683 has open-drain outputs (RXD and ERR-B pins) that allow the user to use external pull-up resistors to the required supply voltage; this can be 5V or 3.3V.

To reduce EME, the rise and fall slope are limited. Together with matched CANL and CANH output-stages, this allows the use of an unshielded twisted pair or a parallel pair of wires for the bus lines. The symmetry of the outputs is guaranteed through the parameters VCM-peak and VCM-step.

7.2 Failure Detector

The failure detector is fully active in the normal operating mode. After the detection of a single bus failure the detector switches to the appropriate mode. The different wiring failures are depicted in Figure 4. The figure also indicates the effect of the different wiring failures on the transmitter and the receiver. The detection circuit itself is not depicted.

The differential receiver threshold voltage is typically set at 3V (VCC = 5V). This ensures correct reception with a noise margin as high as possible in the normal operating mode and in the event of failures 1, 2, 4, and 6a. These failures, or recovery from them, do not destroy ongoing transmissions. During the failure, reception is still done by the differential receiver and the transmitter stays fully active.

To avoid false triggering by external RF influences the single-wire modes are activated after a certain delay time. When the bus failure disappears for an other time delay, the transceiver switches back to differential mode.

The failure detection logic automatically selects a suitable transmission mode, differential or single-wire transmission.

Together with the transmission mode, the failure detector will configure the output stages in such a way that excessive current are avoided and that the circuit returns to normal operation when the error is removed.

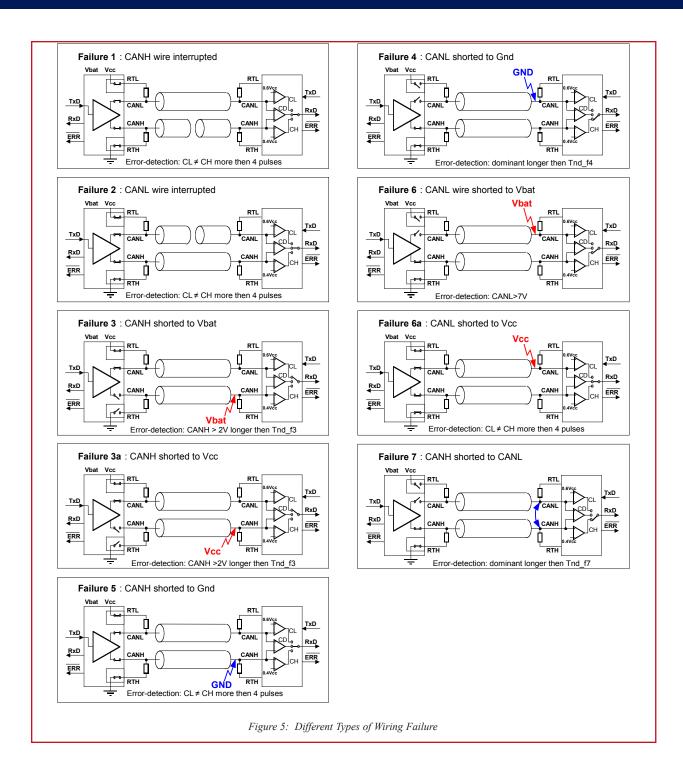
A high common-mode range for the differential and single ended receiver guarantees reception under worst case conditions and together with the integrated filter the circuit realizes a excellent immunity against EMS. The receivers connected to pins CANH and CANL have threshold voltages that ensure a maximum noise margin in single-wire mode.

A timer has been integrated at pin TXD. This timer prevents the AMIS-41682 from driving the bus lines to a permanent dominant state.

When one of the bus failures 3, 5, 6, 6a, and 7 is detected, the defective bus wire is disabled by switching off the affected bus termination and the respective output stage. A wake-up from sleep mode via the bus is possible either via a dominant CANH or CANL line. This ensures that a wake-up is possible even if one of the failures 1 to 7 occurs. If any of the wiring failure occurs, the output signal on pin ERR will become low. On error recovery, the output signal on pin ERR will become high again.

During all single-wire transmissions, the EMC performance (both immunity and emission) is worse than in the differential mode. The integrated receiver filters suppress any HF noise induced into the bus wires. The cut-off frequency of these filters is a compromise between propagation delay and HF suppression. In the single-wire mode, LF noise cannot be distinguished from the required signal.





7.3 Low Power Modes

The transceiver provides three low power modes, which can be entered and exited via pins STB and EN (see Figure 5). (Go-to-sleep mode is only a transition mode)

The sleep mode is the mode with the lowest power consumption. Pin INH is switched to high-impedance for deactivation of the external

voltage regulator. Pin CANL is biased to the battery voltage via pin RTL. If the supply voltage is provided pins RXD and ERR will signal the wake-up interrupt signal.

The standby mode will react the same as the sleep mode but with a high-level on pin INH.



The power-on standby mode is the same as the standby mode with the battery power-on flag instead of the wake-up interrupt signal on pin ERR. The output on pin RXD will show the wake-up interrupt. This mode is only for reading out the power-on flag.

Wake-up request is detected by the following events:

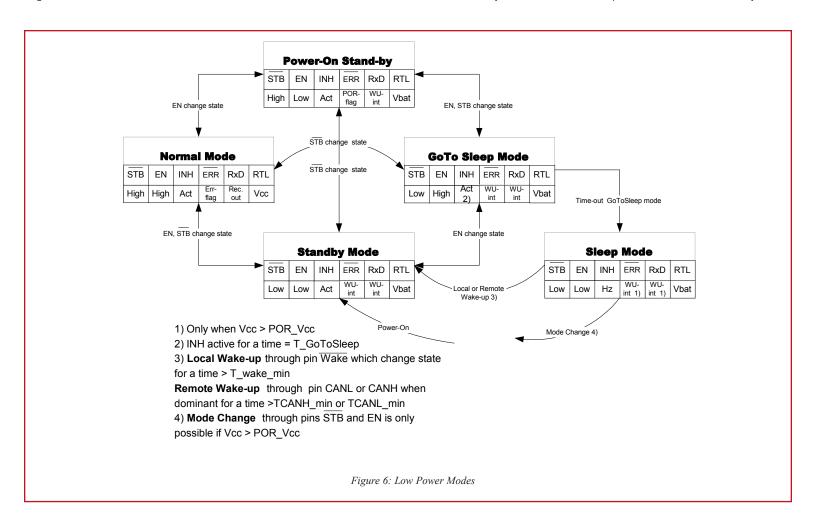
- Power-on (Vbat was below the battery POR-level of 1V)
- Local wake-up: Rising or falling edge on input WAKE (Levels maintained for a certain period)
- Remote wake-up: A message with five consecutive dominant bits

On a wake-up request the transceiver will set the output on pin INH high which can be used to activate the external supply voltage regulator.

If VCC is provided the wake-up request can be read on the ERR or RXD outputs, so the external microcontroller can wake-up the transceiver (switch to normal operating mode) via pins STB and EN.

In the low power modes the failure detection circuit remains partly active to prevent an increased power consumption in the event of failures 3, 3a, 4, and 7.

The go-to-sleep-mode is only a transition mode. The pin INH stays active for a limited time. During this time the circuit can still go to an other low-power-mode. After this time the circuit go to the sleep-mode. Once VCC is below the threshold level of POR, the signals on pins STB and EN will internally be set to low-level to provide fail safe functionality.



7.4 Power-on

After power-on (VBAT switched on) the signal on pin INH will become high and an internal power-on flag will be set. This flag can be read in

the power-on standby mode via pin ERR (STB = 1; EN = 0) and will be reset by entering the normal operating mode.



7.5 Protections

A current limiting circuit protects the transmitter output stages against short circuit to positive and negative battery voltage. If the junction temperature exceeds a maximum value, the transmitter output stages are disabled. Because the transmitter is responsible for the major part of the power dissipation, this will result in a reduced power dissipation

and hence a lower chip temperature. All other parts of the IC will remain operating.

The pins CANH and CANL are protected against electrical transients which may occur in an automotive environment.

8.0 Electrical Characteristics

8.1 Definitions

All voltages are referenced to GND (pin 13). Positive currents flow into the IC. Sinking current means that the current is flowing into the pin. Sourcing current means that the current is flowing out of the pin.

8.2 Absolute Maximum Ratings

Stresses above those listed in this clause may cause permanent device failure. Exposure to absolute maximum ratings for extended periods may effect device reliability.

Table 4: Absolute Maximum Ratings

Symbol	Parameter	Min.	Max.	Unit
VCC	Supply voltage on pin VCC	-0.3	+6	V
VBAT	Battery voltage on pin BAT	-0.3	+40	V
Vdig	DC voltage on pins EN, STB-B, ERR-B, TxD, RxD	-0.3	VCC + 0.3	V
VCANH-L	DC voltage on pins CANH, CANL	-40	+40	V
Vtran-CAN	Transient voltage on pins CANH and CANL (Figure 9) note 1	-350	+350	V
VWAKE	DC input voltage on pin WAKE		VBAT + 0.3	V
IWAKE	DC input current on pin WAKE	-15		mA
VINH	DC output voltage on pin INH	-0.3	VBAT + 0.3	V
VRTH-L	DC voltage on pin RTH, RTL	-40	40	V
RRTH	Termination resistance on pin RTH	500	16000	Ω
RRTL	Termination resistance on pin RTL	500	16000	Ω
Tjunc	Maximum junction temperature	-40	+150	°C
Vesd	Electrostatic discharge voltage (CANH and CANL pin) HBM; note 2 Electrostatic discharge voltage (other pins) HBM; note 2 Electrostatic discharge voltage; machine model; note 3	-8.0 -4.0 -500	+8.0 +4.0 +500	kV kV V

Notes:

- 1. The applied transients shall be in accordance with ISO 7637 part 1, test pulses 1, 2, 3a, and 3b.
- 2. Equivalent to discharging a 100pF capacitor through a 1.5kOhm resistor.
- 3. Equivalent to discharging a 200pF capacitor through a 100hm resistor and a $0.75\mu H$ coil.

8.3 Thermal Characteristics

Table 5: Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
Rth (vj-a)	Thermal resistance from junction to ambient in SSOP14 package (2 layer PCB)	In free air	140	K/W
Rth (vj-s)	Thermal resistance from junction to substrate of bare die	In free air	30	K/W



8.4 Characteristics

 V_{CC} = 4.75V to 5.25V; V_{BAT} = 5V to 50V; T_{junc} = -40°C to +150°C; unless otherwise specified.

Table 6: Characteristics

Normal operating mode; V1XD = 0V (dominant); no load 1 8 12 mA VCC rising VCC falling 2.45 V RBAT	Symbol Supplies Vcc Vbat	Parameter	Conditions	Min.	Тур.	Max.	Unit
LANG_VCC Forced low power mode VCC falling VCC fa	ICC	Supply current					
Battery current on pin BAT	LAG_Vcc	Forced low power mode		2.45		4.5	
FLAG_VBAT POR-level for pin Vbat For setting power-on flag For not setting power-on flag S. 2.1 v V V V V V Fins STB, EN and TXD VII High-level input voltage Final STB Final	IBAT	Battery current on pin BAT	5000hm between RTH - CANH; VBAT = WAKE = INH = 12V;				
For not setting power-on flag 3.5 2.4 1 V	ICC + IBAT	Supply current plus battery current	Low power modes; Vcc = 5V; VBAT = VWAKE = VINH = 12V		30	60	μΑ
VIH High-level input voltage	FLAG_VBAT	POR-level for pin Vbat		3.5		1	
VIL Low-level input voltage -0.3 0.3 x Vcc V	Pins STB, EN and T	XD					
FPU-H High-level input current pin TXD TXD = 0.7 * Vcc -10 -200 μA FPU-L Low-level input current pin TXD TXD = 0.3 * Vcc -80 -800 μA FPU-L Low-level input current pin TXD TXD = 0.3 * Vcc -80 -800 μA FPU-L Low-level input current pin TXD TXD = 0.3 * Vcc -80 -800 μA FPU-L Low-level input current pin EN and STB-B 1V 190 360 600 KΩ FPU-L TXD Dominant time-out for TxD Normal mode; VtxD = 0V 0.75 4 ms FPU-L TXD TXD TXD TXD Normal mode; VtxD = 0V 0.75 4 ms FPU-L TXD	VIH	High-level input voltage		0.7 x Vcc		6.0	V
FPU-L Low-level input current pin TXD TXD = 0.3 * Vcc -80 -800 μA	VIL	Low-level input voltage		-0.3		0.3 x Vcc	V
R-PD Pull-down resistor at pin EN and STB-B 1V 190 360 600 KΩ T_Dis_TxD Dominant time-out for TxD Normal mode; VtxD = 0V 0.75 4 ms T_GoToSleep Minimum hold-time for Go-To-Sleep mode 5 50 μs Pins RXD and ERR-B VCC - 0.9 VCC V VCC V VCC V VCC V V	I-PU-H	High-level input current pin TXD	TXD = 0.7 * Vcc	-10		-200	μΑ
T_Dis_TxD Dominant time-out for TxD Normal mode; VtxD = 0V 0.75 4 ms T_GoToSleep Minimum hold-time for Go-To-Sleep mode 5 5 50 μs Pins RXD and ERR-B VOH High-level output voltage Isource = -1mA VCC - 0.9 VCC V Low-level output voltage Isink = 1.6mA 0 0 0.4 V Isink = 7.5mA 0 0 0.4 V Isink = 1.6mA 0 0 0.4 V Isink = 7.5mA 0 0 0.4 V Isink = 1.6mA 0 0 0.4 V Isink = 7.5mA 0 0 0.4 V Isink = 1.6mA 0 0 0 0 0.4 V Isink = 1.6mA 0	I-PU-L	Low-level input current pin TXD	TXD = 0.3 * Vcc	-80		-800	μΑ
T_GoToSleep Minimum hold-time for Go-To-Sleep mode 5 50 µs Pins RXD and ERR-B VOH High-level output voltage Isource = -1mA VCC - 0.9 VCC V VOL Low-level output voltage Isink = 1.6mA 0 0.4 1.5 V Pin WAKE IIL Low-level input current VWAKE = 0V; VBAT = 27V -10 -1 µA Vth (WAKE) Wake-up threshold voltage VSTB-B = 0V 2.5 3.2 3.9 V T_Wake_Min Minimum time on pin wake (debounce time) VBAT = 12V; low power mode; for rising and falling edge 7 38 µs Pin INH Delta_VH High-level voltage drop IINH = 0.18mA 0.8 V	R-PD	Pull-down resistor at pin EN and STB-B	1V	190	360	600	ΚΩ
Pins RXD and ERR-B VOH High-level output voltage Isource = -1mA VCC - 0.9 VCC V VOL Low-level output voltage Isink = 1.6mA 0 0.4 1.5 V Pin WAKE IIIL Low-level input current VWAKE = 0V; VBAT = 27V -10 -1 μA Vth (WAKE) Wake-up threshold voltage VSTB-B = 0V VBAT = 12V; low power mode; for rising and falling edge 7 38 μs Pin INH Delta_VH High-level voltage drop IINH = 0.18mA	T_Dis_TxD	Dominant time-out for TxD	Normal mode; VtxD = 0V	0.75		4	ms
VOH High-level output voltage Isource = -1mA VCC - 0.9 VCC V VOL Low-level output voltage Isink = 1.6mA 0 0.4 V Isink = 1.6mA 0 0 0.4 V Isink = 7.5mA 0 0 1.5 V Pin WAKE IIL Low-level input current VWAKE = 0V; VBAT = 27V -10 -1 μA Vth (WAKE) Wake-up threshold voltage VSTB-B = 0V 2.5 3.2 3.9 V T_Wake_Min Minimum time on pin wake (debounce time) VBAT = 12V; low power mode; for rising and falling edge 7 38 μs Pin INH Delta_VH High-level voltage drop IINH = 0.18mA 0.8 V	T_GoToSleep	Minimum hold-time for Go-To-Sleep mode		5		50	μs
VOL Low-level output voltage Sink = 1.6mA 0 0.4 V Isink = 7.5mA 0 0.4 1.5 V Pin WAKE III	Pins RXD and ERR-	В					
VOL Low-level output voltage Isink = 7.5mA 0 1.5 V Pin WAKE IIIL Low-level input current VWAKE = 0V; VBAT = 27V -10 -1 μA Vth (WAKE) Wake-up threshold voltage VSTB-B = 0V 2.5 3.2 3.9 V T_Wake_Min Minimum time on pin wake (debounce time) VBAT = 12V; low power mode; for rising and falling edge 7 38 μs Pin INH Delta_VH High-level voltage drop IINH = 0.18mA 0.8 V	VOH	High-level output voltage	Isource = -1mA	VCC - 0.9		VCC	V
IIILLow-level input currentVWAKE = 0V; VBAT = 27V-10-1μAVth (WAKE)Wake-up threshold voltageVSTB-B = 0V2.53.23.9VT_Wake_MinMinimum time on pin wake (debounce time)VBAT = 12V; low power mode; for rising and falling edge738μsPin INHDelta_VHHigh-level voltage dropIINH = 0.18mA0.8V	VOL	Low-level output voltage					
Vth (WAKE) Wake-up threshold voltage VSTB-B = 0V VSTB-B = 0V VBAT = 12V; low power mode; for rising and falling edge 7 38 μs Pin INH Delta_VH High-level voltage drop IINH = 0.18mA Oscilopting threshold voltage voltage drop VSTB-B = 0V VSTB-B = 0V VBAT = 12V; low power mode; for rising and falling edge 7 38 μs No.8 V	Pin WAKE						
T_Wake_Min Minimum time on pin wake (debounce time) VBAT = 12V; low power mode; for rising and falling edge 7 38 µs Pin INH Delta_VH High-level voltage drop IINH = 0.18mA 0.8 V	IIL	Low-level input current	VWAKE = 0V; VBAT = 27V	-10		-1	μΑ
Pin INH Delta_VH High-level voltage drop IINH = 0.18mA 0.8 V	Vth (WAKE)	Wake-up threshold voltage	VSTB-B = 0V	2.5	3.2	3.9	V
Delta_VH High-level voltage drop IINH = 0.18mA 0.8 V	T_Wake_Min	Minimum time on pin wake (debounce time)	VBAT = 12V; low power mode; for rising and falling edge	7		38	μs
	Pin INH						
I_{leak} Leakage current Sleep mode; VINH = 0V 1 μA	Delta_VH	High-level voltage drop	IINH = 0.18mA			0.8	V
	I_leak	Leakage current	Sleep mode; VINH = 0V			1	μΑ

Table 6: Characteristics Continued

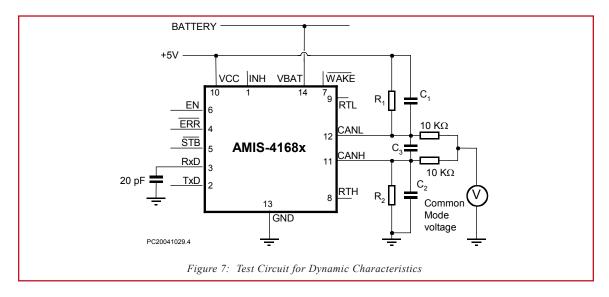
Symbol Pins CANH and	Parameter CANL (receiver)	Conditions	Min.	Тур.	Max.	Unit
Vdiff	Differential receiver threshold voltage	No failures and bus failures 1, 2, 3, and 6a; see Figure 4 VCC = 5V VCC = 4.75V to 5.25V	-3.25 0.65 x Vcc	-3 0.6 x Vcc	-2.75 0.55 x Vcc	V
VseCANH	Single-ended receiver threshold voltage on pin CANH	Normal operating mode and failures 4, 6 and 7 VCC = 5V VCC = 4.75V to 5.25V	1.6 0.32 x Vcc	1.775 0.355 x Vcc	1.95 0.39 x Vcc	V
VseCANL	Single-ended receiver threshold voltage on pin CANL	Normal operating mode and failures 3 and 3a VCC = 5V VCC = 4.75V to 5.25V	3 0.61 x Vcc	3.2 0.645 x Vcc	3.4 0.68 x Vcc	V
Vdet(CANL)	Detection threshold voltage for short circuit to battery voltage on pin CANL	Normal operating mode	6.5	7.3	8	V
Vth(wake)	Wake-up threshold voltage On pin CANL On pin CANH	Low power modes Low power modes	2.5 1.1	3.2 1.8	3.9 2.25	V
DVth(wake)	Difference of wake-up threshold voltages	Low power modes	0.8	1.4		V
Pins CANH and C	CANL (transmitter)					
VO(reces)	Recessive output voltage On pin CANH On pin CANL	VTXD = VCC RRTH < $4k\Omega$ RRTL < $4k\Omega$	Vcc - 0.2		0.2	V
VO(dom)	Dominant output voltage On pin CANH On pin CANL	VTXD = 0V; VEN = VCC ICANH = -40mA ICANL = 40mA	Vcc - 1.4		1.4	V
IO(CANH)	Output current on pin CANH	Normal operating mode; VCANH = 0V; VTXD = 0V Low power modes: VCANH = 0V; VCC = 5V	-100 -1	-80 0	-45 1	mA μA
IO(CANL)	Output current on pin CANL	Normal operating mode; VCANL = 14V; VTXD = 0V Low power modes; VCANL = 12V; VBAT = 12V	45 -1	80	110 1	mA μA
Pins RTH and RTI	_					
Rsw(RTL)	Switch-on resistance between pin RTL and VCC	Normal operating mode; I(RTL) > -10mA			100	Ω
Rsw(RTH)	Switch-on resistance between pin RTH and ground	Normal operating mode; I(RTH) > 10mA			100	Ω
VO(RTH)	Output voltage on pin RTH	Low power modes; IO = 1mA			1.0	V
IO(RTL)	Output current on pin RTL	Low power modes; VRTL = 0V	-1.25		-0.3	mA
Ipu(RTL)	Pull-up current on pin RTL	Normal operating mode and failures 4, 5 and 7; VRTL = 0V		-75		μА
lpd(RTH)	Pull-down durrent on pin RTH	Normal operating mode and failures 3 and 3a		-75		μА
Thermal shutdow						
Tj	Junction temperature	For shutdown	150		180	°C

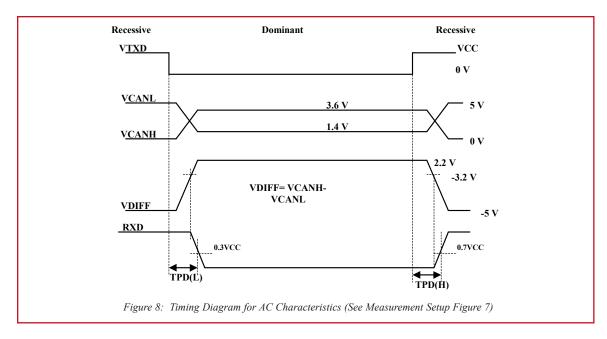
8.5 Timing Characteristics

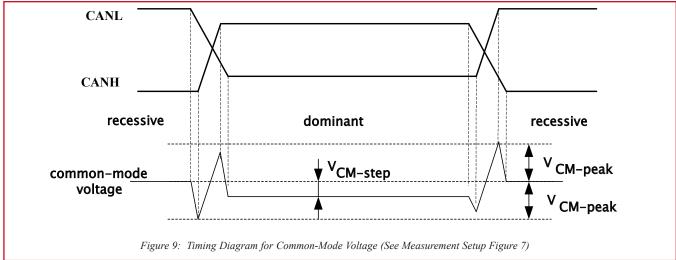
 V_{CC} = 4.75V to 5.25V; V_{BAT} = 5V to 27V; V_{STB} = V_{CC} ; T_{junc} = -40°C to 150°C; unless otherwise specified.

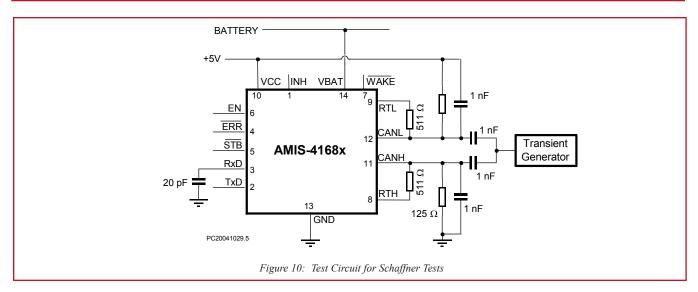
Table 7: Timing Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
tt(r-d)	CANL and CANH output transition time for recessive-to-dominant	10% to 90%; C1 = 10nF; C2 = 0; R1 = 100Ω; see Figure 6	0.35	0.60	1.4	μs
tt(d-r)	CANL and CANH output transition time for dominant-to-recessive	10% to 90%; C1 = 1nF; C2 = 0; R1 = 100Ω; see Figure 5	0.2	0.3	0.7	μs
tPD(L)	Propagation delay TXD to RXD (LOW)	No failures and failures 1, 2, 4, and 6a; see Figure 6, 7 C1 = 1nF; C2 = 0; R1 = 100Ω C1 = C2 - 3.3nF; R1 = 100Ω Failures 3, 3a, 5, 6, and 7; see Figure 6, 7 C1 = 1nF; C2 = 0; R1 = 100Ω C1 = C2 = 3.3nF; R1 = 100Ω		0.75 1.00 0.85 1.1	1.5 1.75 1.85 1.7	μs μs μs μs
tPD(H)	Propagation delay TXD to RXD (HIGH)	No failures and failures 1, 2, 4, and 6a; see Figure 6, 7 C1 = 1nF; C2 = 0; R1 = 100Ω C1 = C2 = 3.3 nF; R1 = 100Ω Failures 3, 3a, 5, 6, and 7; see Figure 6, 7 C1 = 1 nF; C2 = 0 ; R1 = 100Ω C1 = C2 = 3.3 nF; R1 = 100Ω		1.2 2.5 1.1 1.5	1.9 3.3 1.7 2.2	μs μs μs μs
tCANH(min)	Minimum dominant time for wake-up on pin CANH	Low power modes; VBAT = 12V	7		38	μs
tCANL(min)	Minimum dominant time for wake-up on pin CANL	Low power modes; VBAT = 12V	7		38	μs
tdet	Failure detection time	Normal mode Failure 3 and 3a Failure 4, 6 and7 Low power modes; VBAT = 12V Failure 3 and 3a Failure 5 and 7	1.6 0.3 1.6 0.3		8.0 1.6 8.0 1.6	ms ms ms
trec	Failure recovery time	Normal mode Failure 3 and 3a Failure 4 and 7 Failure 6 Low power modes; VBAT = 12V Failures 3, 3a, 5, and 7	0.3 7 125		1.6 38 750	ms μs μs
Dpc	Pulse-count difference between CANH and CANL	Normal mode and failures 1, 2, 3, and 6a Failure detection (pin ERR becomes LOW) Failure recovery		4 4		

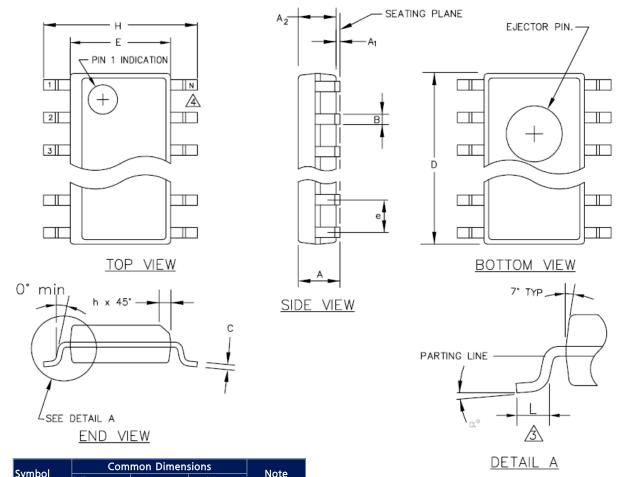








9.0 Package Outline



Symbol	Con	Common Dimensions				
Symbol	Min.	Nom.	Max.	Note		
А	.061	.064	.068			
A ₁	.004	.006	0.010			
A_2	.055	.058	.061			
В	.0138	.016	.020			
С	.0075	.008	.0098			
D		See Variations	5	1		
E	.150	.155	.157			
е		.050 BSC				
Н	.230	.236	.244			
h	.010	.013	.016			
L	.016	.025	.035			
N		See Variations	5	2		
α°	0°	5°	8°			
Variations	Variations					
		1		2		

variations				
		1		2
	ا)		N
Note	Min.	Nom.	Max.	
AA	.189	.194	.196	8
AB	.337	.342	.344	14
AC	.386	.391	.393	16

Notes:

- 1. Maximum die thickness allowable is .015.
- 2. Dimensioning and tolerances per ANSI.Y14.5M 1982.
- 3. "L" is the length of terminal for soldering to a substrate.
- 4. "N" is the number of terminal positions.
- 5. Formed leads shall be planar with respect to one another within .003 inches at seating plane.
- 6. Country of origin location and ejector pin on package bottom is optional and depend on assemble location.
- 7. Controlling dimension: inches.

Figure 11: SOIC-14 - Plastic Small Outline; 14 Leads; Body Width 150 mil; JEDEC: MS-012

10.0 Soldering

10.1 Introduction

Introduction to soldering surface mount packages. This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our "Data Handbook IC26; Integrated Circuit Packages" (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

10.2 Reflow Soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating,

soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 $^{\circ}$ C. The top-surface temperature of the packages should preferably be kept below 230 $^{\circ}$ C.

10.3 Wave Soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printedcircuit board;
 - smaller than 1.27mm, the footprint longitudinal axis must be

parallel to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves at the downstream end.

 For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is four seconds at 250°C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

10.4 Manual Soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300°C.

When using a dedicated tool, all other leads can be soldered in one operation within two to five seconds between 270 and 320°C.



Table 8: Soldering Process

Dockomo	Solderin	Soldering Method		
Package	Wave	Reflow (1)		
BGA, SQFP	Not suitable	Suitable		
HLQFP,HSQFP, HSOP, HTSSOP, SMS	Not suitable (2)	Suitable		
PLCC (3), SO, SOJ	Suitable	Suitable		
LQFP, QFP, TQFP	Not recommended (3)(4)	Suitable		
SSOP, TSSOP, VSO	Not recommended (5)	Suitable		

Notes:

- 1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods."
- 2. These packages are not suitable for wave soldering as a solder joint between the printed circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65mm.
- 5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5mm.

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